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LIST OF PUBLICATIONS

1. C Usha, P Vimala, **T.S.Arun Samuel**, MK Pandian, “A Novel 2-D Analytical Model For The Electrical Characteristics Of A Gate-All-Around Heterojunction Tunnel Field-Effect Transistor Including Depletion Regions” Journal Of Computational Electronics 25-04-2020 | Issue 3/2020
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